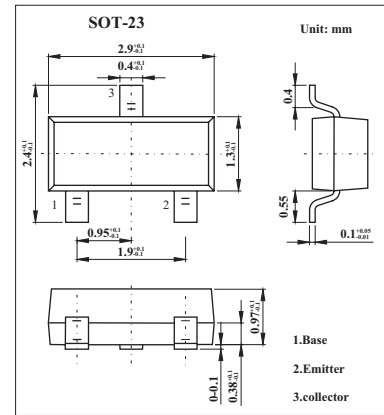


PNP Medium Frequency Transistor

BF550

■ Features

- Low current (max. 25 mA).
- Low voltage (max. 40 V).

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---|---------------|-------------|------------------|
| Collector-base voltage | V_{CB0} | -40 | V |
| Collector-emitter voltage | V_{CE0} | -40 | V |
| Emitter-base voltage | V_{EB0} | -4 | V |
| Collector current | I_C | -25 | mA |
| Peak collector current | I_{CM} | -25 | mA |
| Total power dissipation * | P_{tot} | 250 | mW |
| Storage temperature | T_{stg} | -65 to +150 | $^\circ\text{C}$ |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Operating ambient temperature | R_{amb} | -65 to +150 | $^\circ\text{C}$ |
| Thermal resistance from junction to ambient * | $R_{th\ j-a}$ | 500 | K/W |

* Transistor mounted on an FR4 printed-circuit board.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|--------------------------|-----------|---|-----|-----|------|------|
| Collector cutoff current | I_{CBO} | $I_E = 0; V_{CB} = -30\text{ V}$ | | | -50 | nA |
| Emitter cutoff current | I_{EBO} | $I_C = 0; V_{EB} = -3\text{ V}$ | | | -100 | nA |
| DC current gain | h_{FE} | $I_C = -1\text{ mA}; V_{CE} = -10\text{ V}$ | 50 | | | |
| Base to emitter voltage | V_{BE} | $I_C = -1\text{ mA}; V_{CE} = -10\text{ V}$ | | 750 | | mV |
| Feedback capacitance | C_{re} | $I_C = -1\text{ mA}; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$ | | 0.5 | | pF |
| Transition frequency | f_T | $I_C = -1\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$ | | 325 | | MHz |

■ Marking

| | |
|---------|----|
| Marking | LA |
|---------|----|